

## Poster-2-7

**Progress in the study of rare-earth silicate systems**

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Rare-earth silicates are an interesting class of materials owing their potential for optical (laser diodes, scintillators) and environmental barrier coating (EBC) applications. One of the major difficulties encountered in the synthesis and study of these systems is due to the existence of a relatively large number of chemical phases and polymorphism possible at ambient pressure. Moreover, there is an overlap of the thermodynamic stability ranges of the different polymorphs and/or chemical phases, thus hindering the synthesis of pure phase ceramic materials by conventional solid-state reaction. To overcome these drawbacks and study the intrinsic properties of these systems, one can attempt to prepare these materials in crystal form. We successfully prepared large, high quality, crack-free and pure phase single crystals of  $R_2SiO_5$  ( $R = Dy, Ho$  and  $Er$ ) using a laser-diode-heated floating zone furnace. Here, we present the results of our investigations to optimize the synthesis and crystal growth conditions of  $R_2SiO_5$ , and discuss the properties of these materials [1]. The progress in preparing single crystals of these materials is crucial for the study of the intrinsic structural, chemical and physical properties of rare-earth silicate systems which will open the route for improving the properties of these materials for applications.

[1] V.C. Ciomaga Hatnean et al., Crystal Growth of the  $R_2SiO_5$  Compounds ( $R = Dy, Ho, \text{ and } Er$ ) by the Floating Zone Method Using a Laser-Diode-Heated Furnace, *Crystals* 2023, 13, 1687.